

# BSS192

240 V, P-channel vertical D-MOS transistor

12 December 2014

Product data sheet

## 1. General description

P-channel enhancement mode vertical Double-Diffused Field-Effect Transistor (D-MOSFET) in a SOT89 (SC-62) medium power and flat lead Surface Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Direct interface to Complementary (C-MOS) transistor and Transistor-Transistor Logic (TTL) devices
- Very fast switching
- No secondary breakdown

## 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-240	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-200	mA
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10\text{ V}; I_D = -200\text{ mA}; T_j = 25\text{ °C}$	-	10	12	$\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .

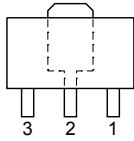
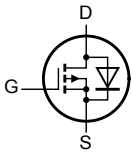


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p style="text-align: center;"><b>SOT89</b></p>	 <p style="text-align: center;"><i>017aaa257</i></p>
2	D	drain		
3	G	gate		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS192	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BSS192	KB

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$		-	-240	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}; t \leq 5\text{ s}$	[1]	-	-340	mA
		$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	-200	mA
		$V_{GS} = -10\text{ V}; T_{amb} = 100\text{ }^\circ\text{C}$	[1]	-	-120	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ }^\circ\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	-800	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$	[2]	-	560	mW
			[1]	-	1	W
		$T_{sp} = 25\text{ }^\circ\text{C}$		-	12.5	W
$T_j$	junction temperature			-55	150	$^\circ\text{C}$
$T_{amb}$	ambient temperature			-55	150	$^\circ\text{C}$
$T_{stg}$	storage temperature			-65	150	$^\circ\text{C}$
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	-200	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

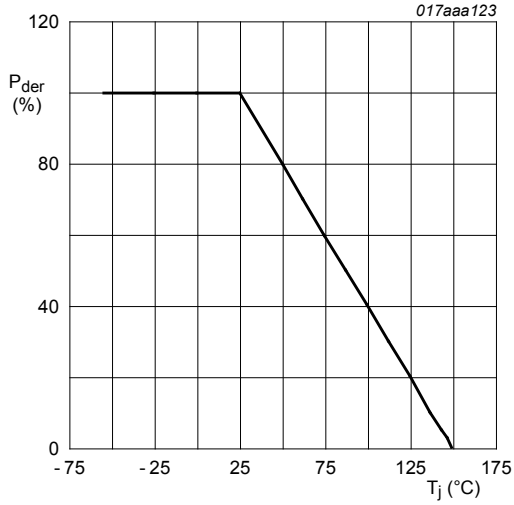


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

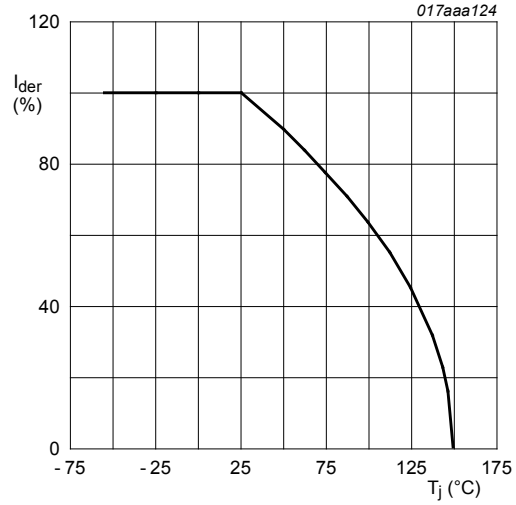
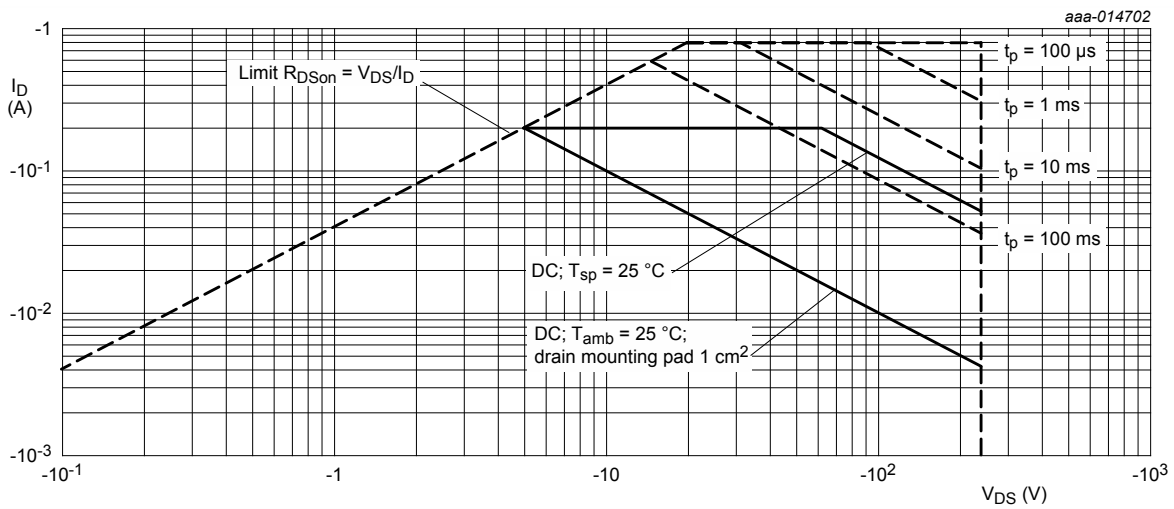


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	194	225	K/W
			[2]	-	108	125	K/W
		t ≤ 5 s	[2]	-	37	42	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	4	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

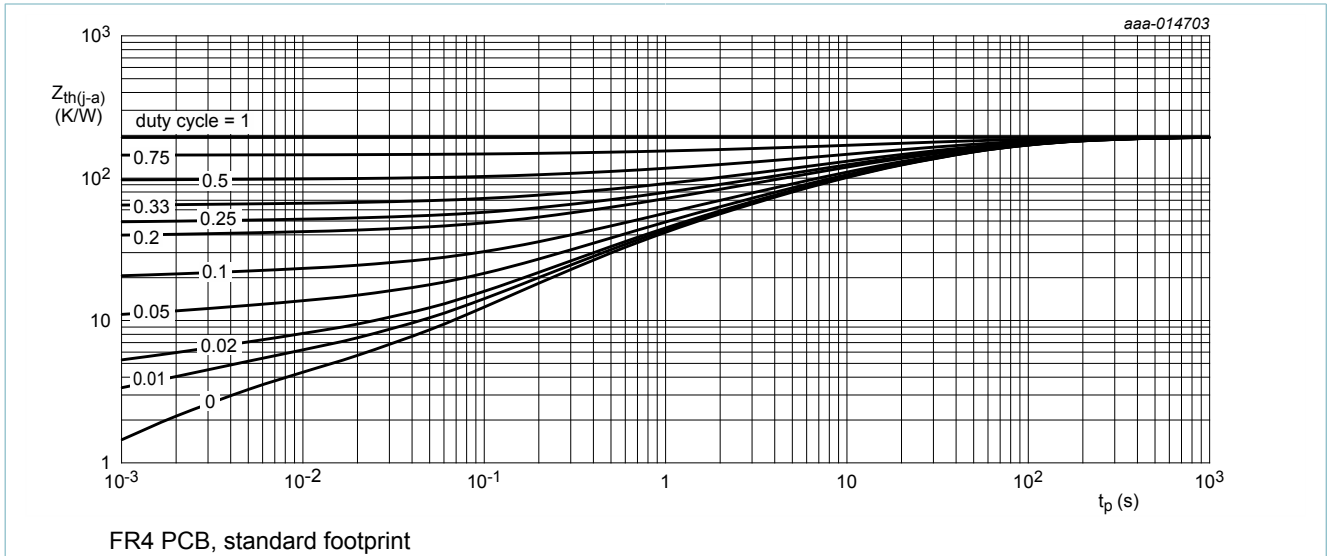


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

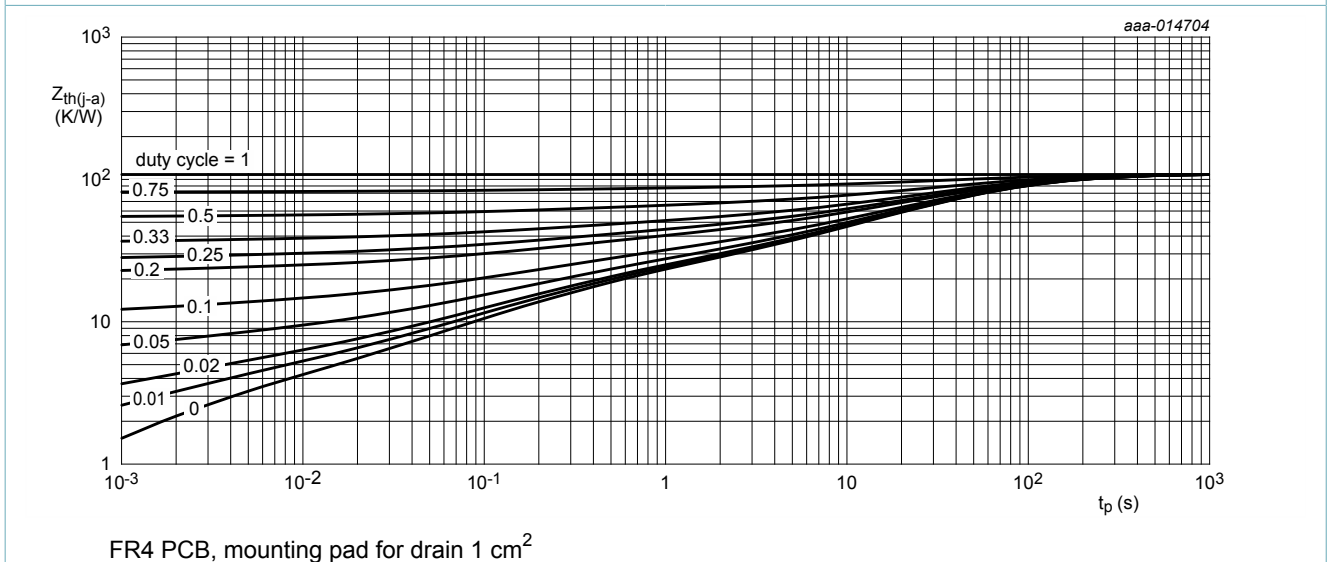
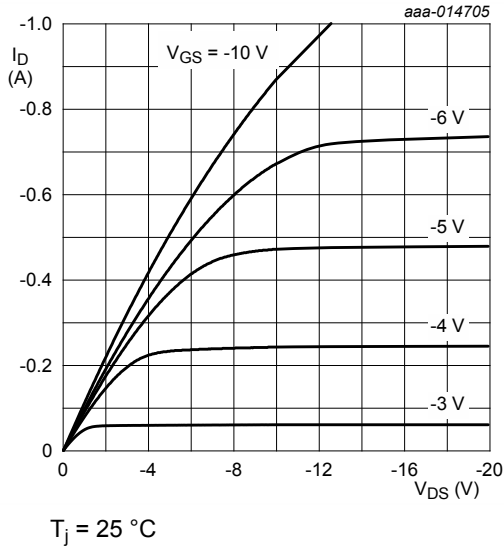


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

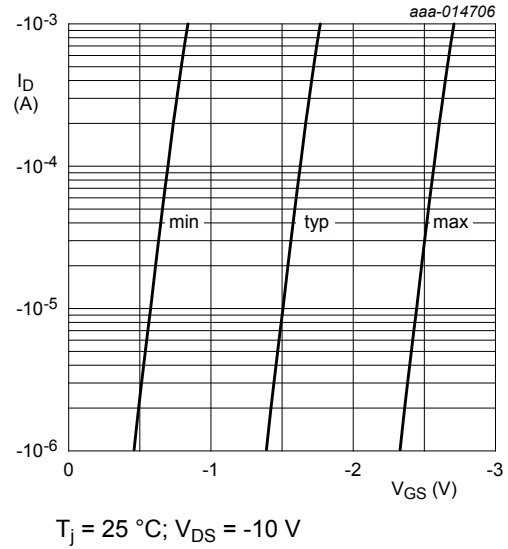
## 10. Characteristics

Table 7. Characteristics

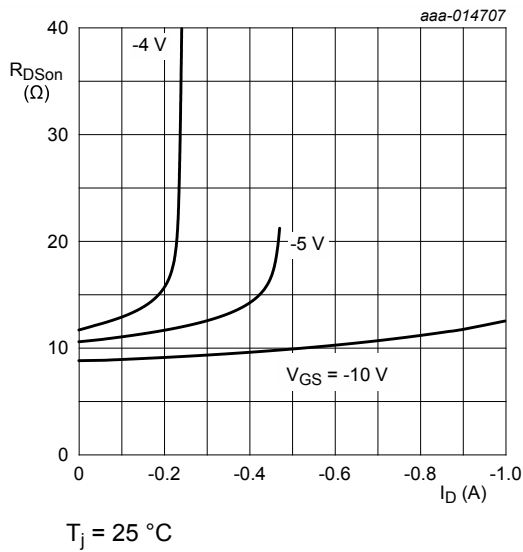
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-240	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	-0.8	-	-2.8	V
$I_{DSS}$	drain leakage current	$V_{DS} = -200 V; V_{GS} = 0.2 V; T_j = 25 \text{ }^\circ C$	-	-0.1	-60	$\mu A$
		$V_{DS} = -60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-200	nA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10 V; I_D = -200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	10	12	$\Omega$
		$V_{GS} = -10 V; I_D = -200 \text{ mA}; T_j = 150 \text{ }^\circ C$	-	21	25	$\Omega$
		$V_{GS} = -4.5 V; I_D = -100 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	13	18	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = -10 V; I_D = -200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	200	-	mS
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -50 V; I_D = -250 \text{ mA}; V_{GS} = -10 V; T_j = 25 \text{ }^\circ C$	-	1.9	5	nC
$Q_{GS}$	gate-source charge		-	0.3	-	nC
$Q_{GD}$	gate-drain charge		-	0.6	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -25 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	55	90	pF
$C_{oss}$	output capacitance		-	20	30	pF
$C_{rss}$	reverse transfer capacitance		-	5	15	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = -50 V; I_D = -250 \text{ mA}; V_{GS} = -10 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	3.2	6
$t_r$	rise time	-		4.6	6	ns
$t_{d(off)}$	turn-off delay time	-		11.7	20	ns
$t_f$	fall time	-		7	12	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = -200 \text{ mA}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.86	1.2	V



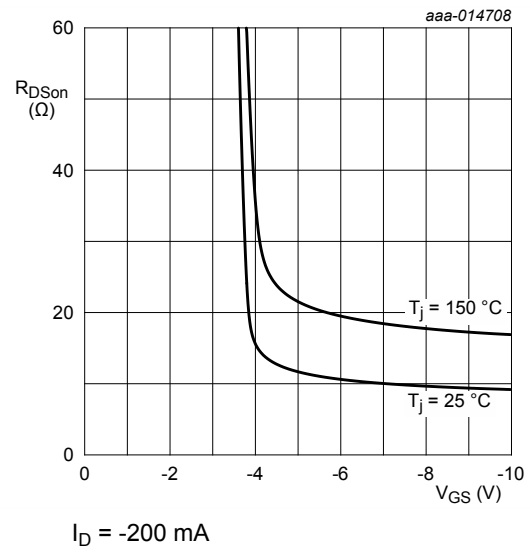
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



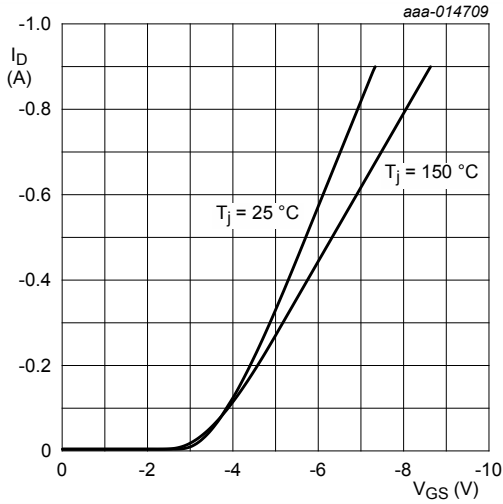
**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**



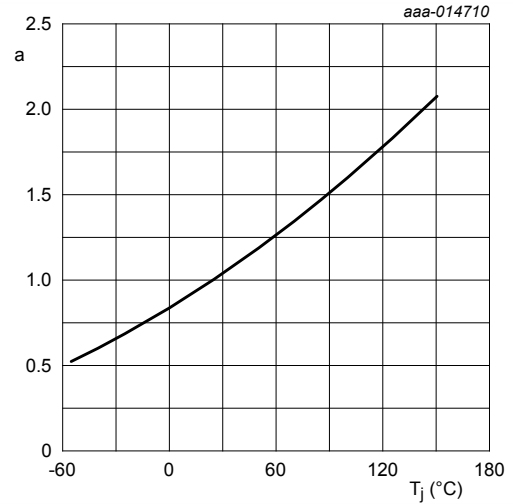
**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**

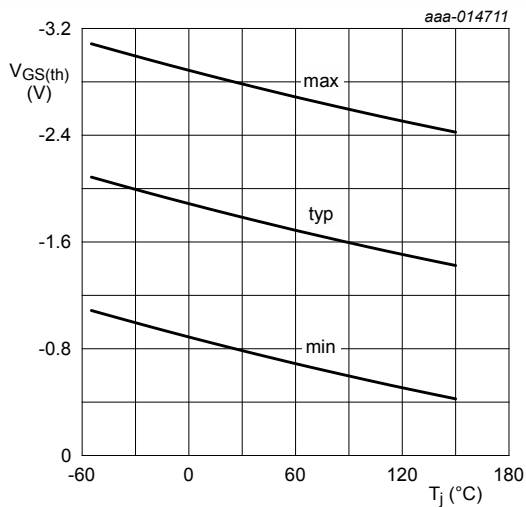


**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



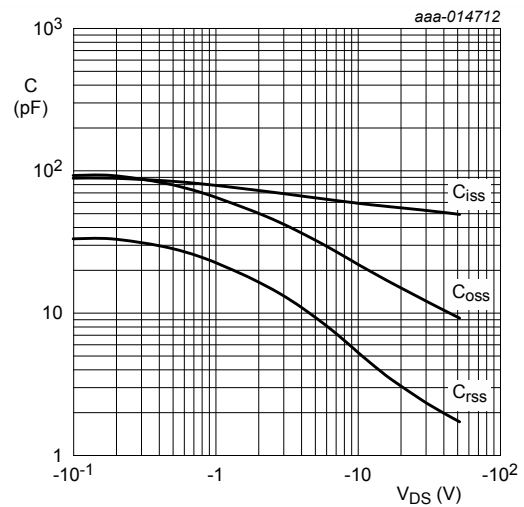
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



**Fig. 12. Gate-source threshold voltage as a function of junction temperature**

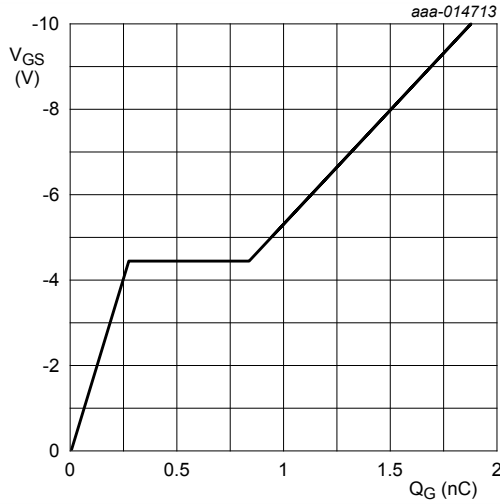
$I_D = -1 \text{ mA}; V_{DS} = V_{GS}$



**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$





$I_D = -0.25 \text{ A}; V_{DS} = -50 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

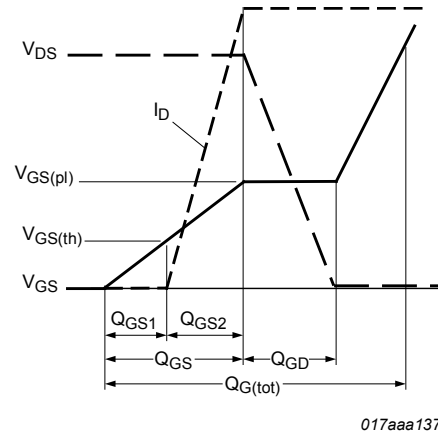
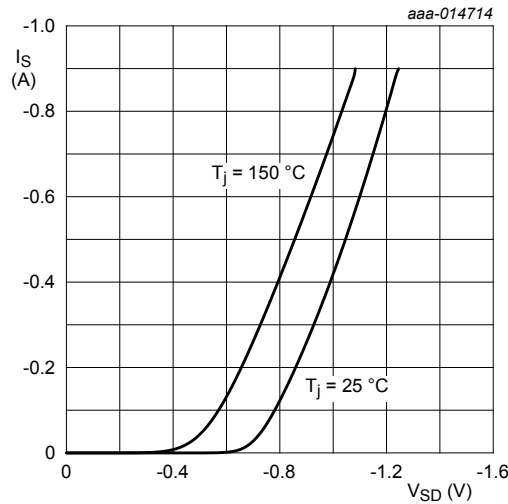


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

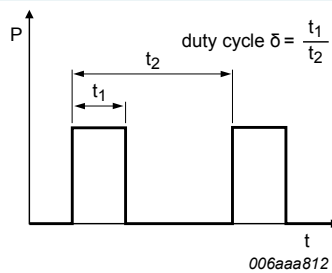


Fig. 17. Duty cycle definition

## 12. Package outline

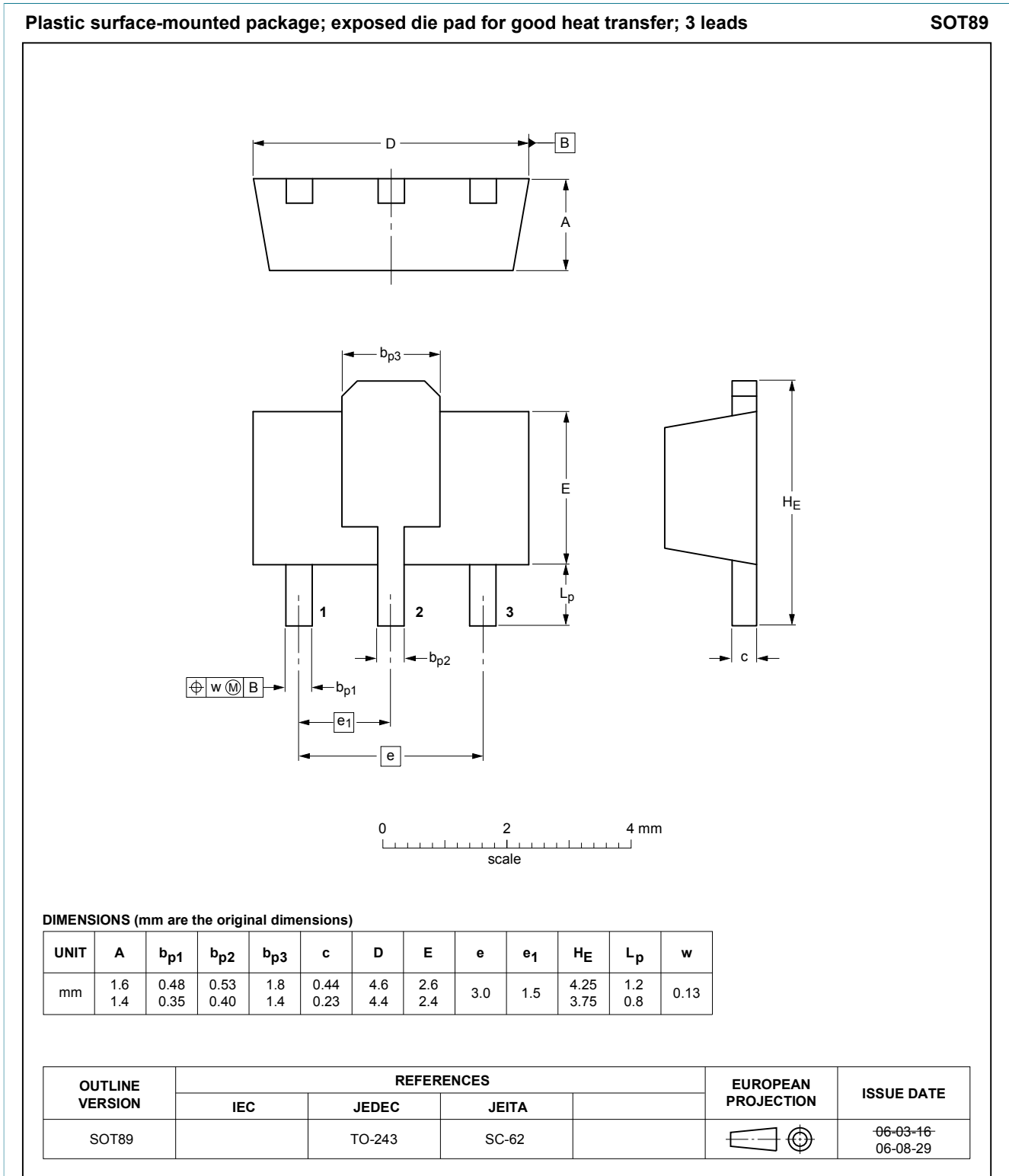


Fig. 18. Package outline SOT89



## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS192 v.4	20141212	Product data sheet	-	BSS192 v.3
Modifications:	<ul style="list-style-type: none"><li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors</li><li>Legal texts have been adapted to the new company name where appropriate</li></ul>			
BSS192 v.3	20021120		-	BSS192 v.2
BSS192 v.2	20020522		-	BSS192 v.1
BSS192 v.1	19970620			-

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### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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